

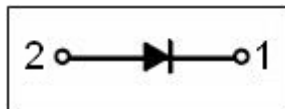
Rev.H Apr.-2018

SOD-323

Silicon Diode in a SOD-323 Plastic Package.

Small signal diode . HF Product.

Switching diodes.



PIN1:Cathode

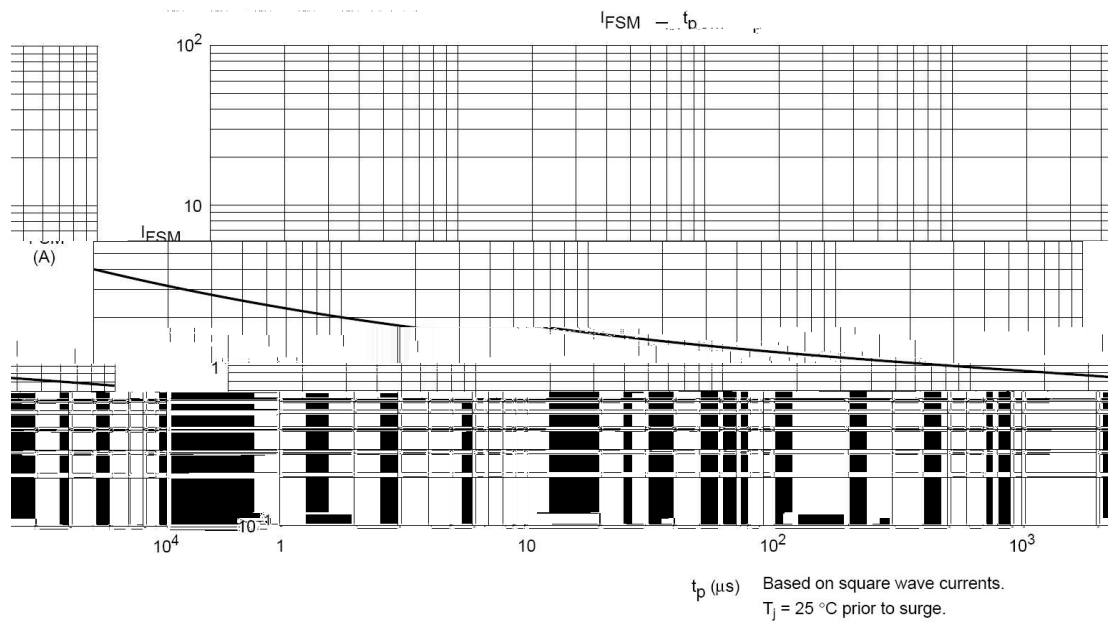
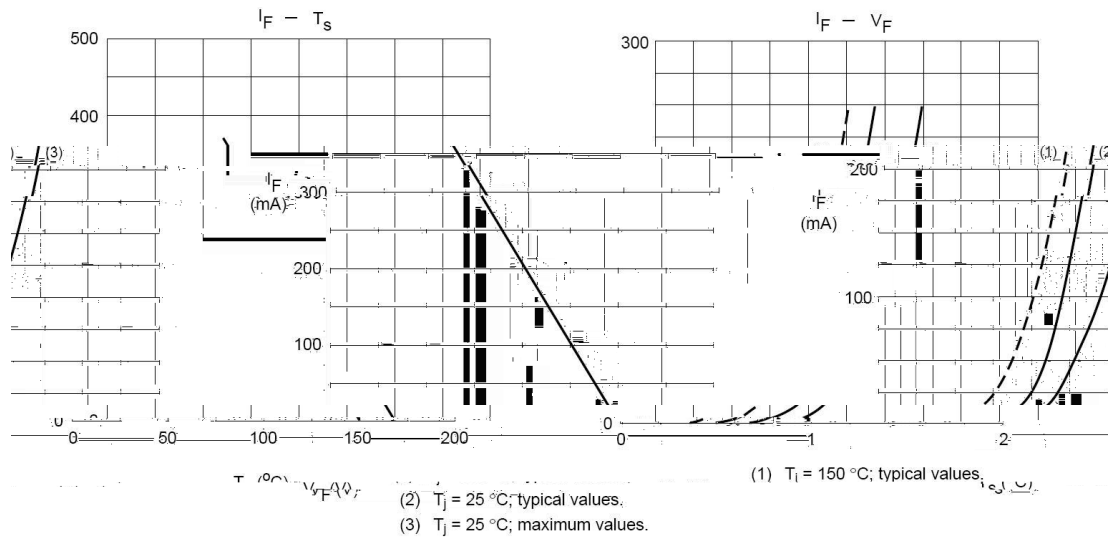
PIN2:Anode

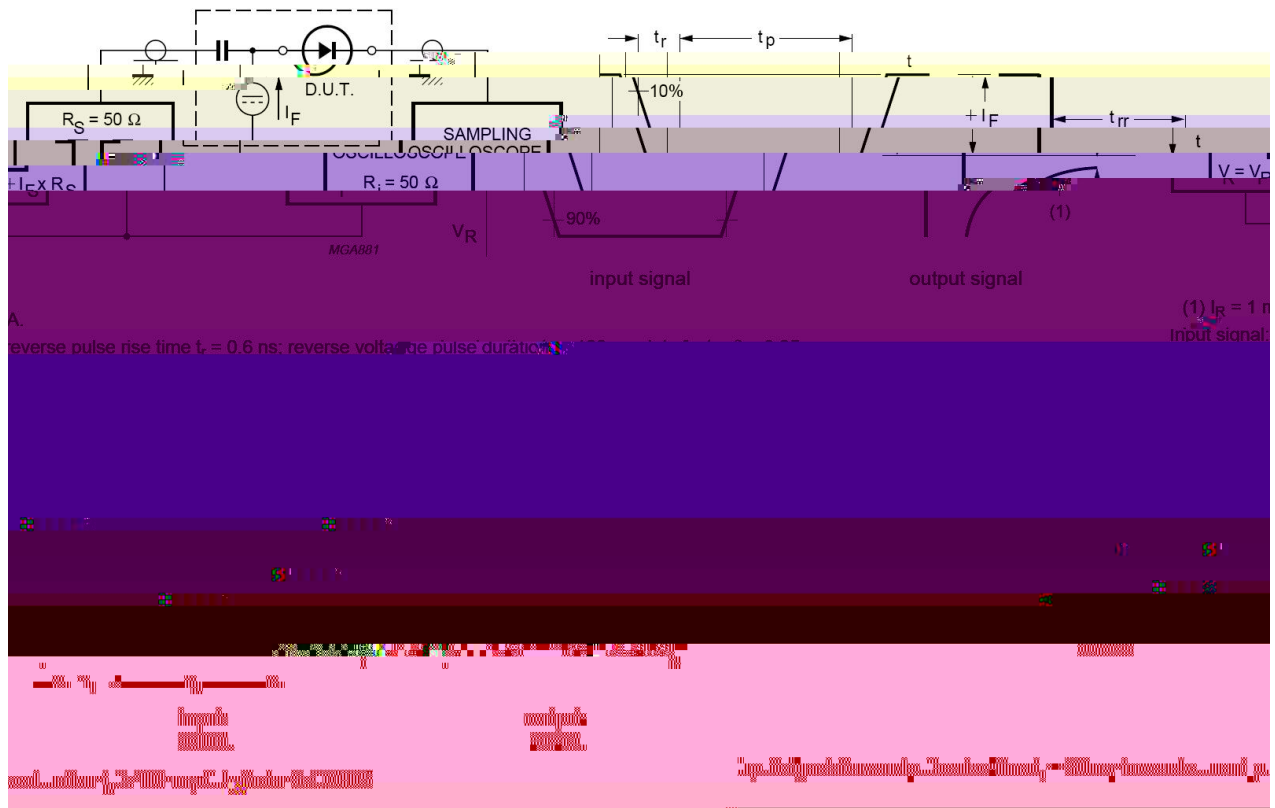
Marking	A6H
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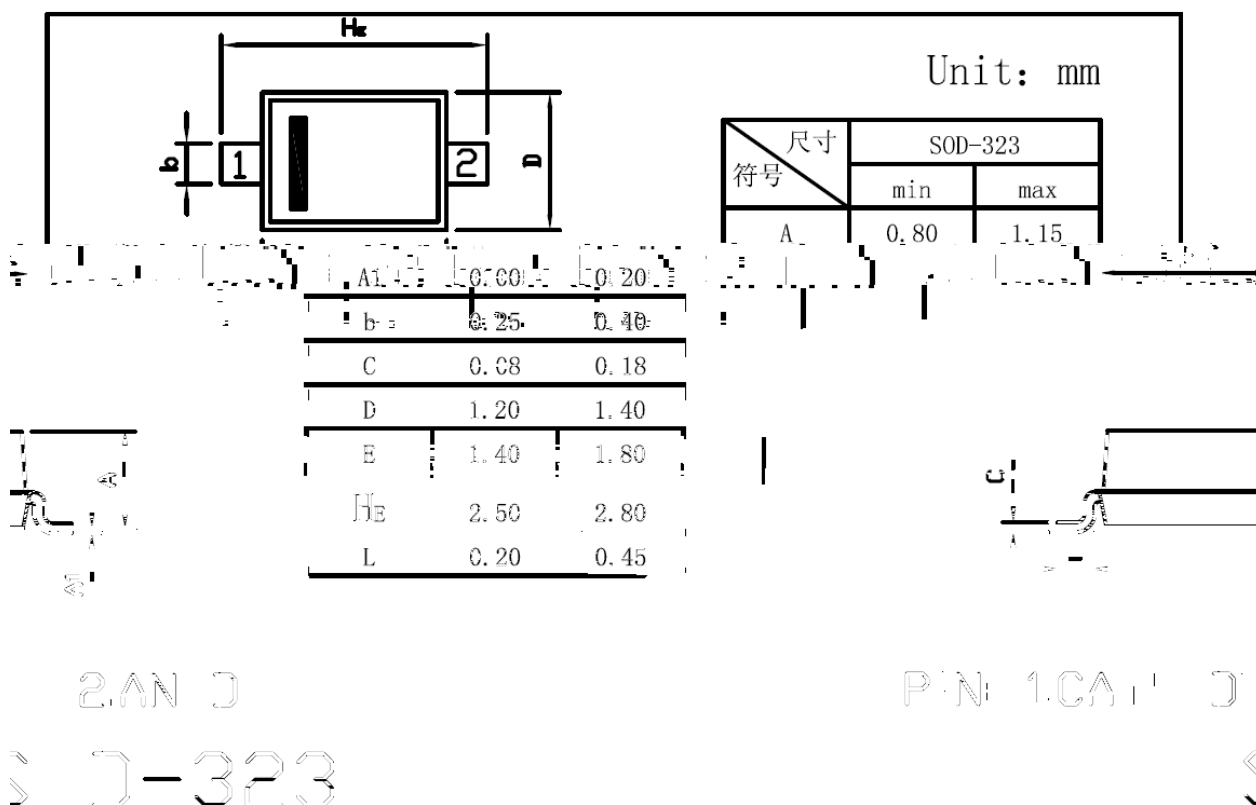
Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}	85	V
Continuous forward current	$I_{F(AV)}$ ($T_s=90^\circ\text{C}$)	250	mA
Non-repetitive peak forward current	$I_{FSM(1)(t=1S)}$	0.5	A
	$I_{FSM(2)(t=1mS)}$	1.0	A
Total power dissipation	P_{tot} ($T_s=90^\circ\text{C}$)	400	mW
Thermal resistance from junction to soldering point	$R_{\theta J-S}$	150	K/W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65~150	$^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=1\text{mA}$			715	mV
		$I_F=10\text{mA}$			855	mV
		$I_F=50\text{mA}$			1.0	V
		$I_F=150\text{mA}$			1.25	V
Reverse Current	I_R	$V_R=25\text{V}$			30	nA
		$V_R=75\text{V}$			1.0	μA
		$V_R=25\text{V}$ $T_j=150^\circ\text{C}$			30	μA
		$V_R=75\text{V}$ $T_j=150^\circ\text{C}$			50	μA
Diode capacitance	C_d	$V_R=0$ $f=1.0\text{MHz}$			1.5	pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=10\text{mA}$ $I_R=1.0\text{mA}$ $R_L=100\Omega$			4.0	ns
Forward recovery voltage	V_{fr}	$I_F=10\text{mA}$ $T_r=20\text{ns}$			1.75	V

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A6

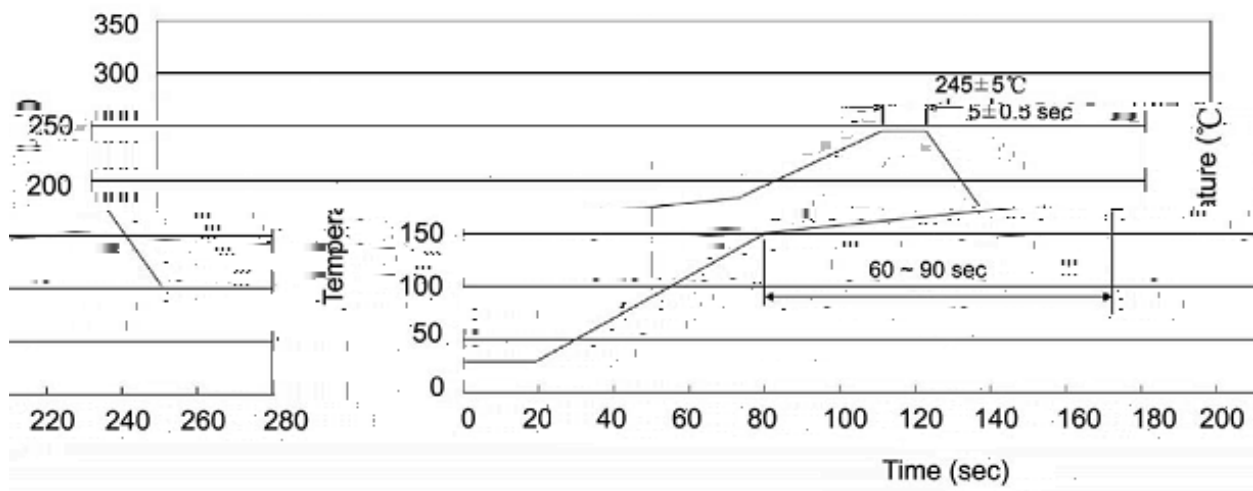
H:

Note:

A6: Product Type Code

H Company Code

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

150 180

60 90sec;

1.Preheating: 150 180 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOD-323	3,000	10	30,000	6	180,000	7" ×8	180×120×180	390×385×205